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Lead-free Green

DMPH6250S

60V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
-60V	155mΩ @ V_{GS} = -10V	-2.4A
	240mΩ @ V_{GS} = -4.5V	-1.9A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Load Switch

Features and Benefits

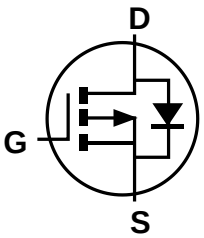
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMPH6250SQ)**

Mechanical Data

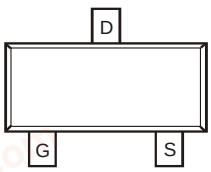
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View



Internal Schematic



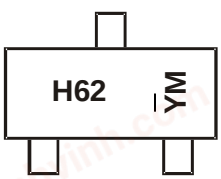
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6250S-7	SOT23	3000/Tape & Reel
DMPH6250S-13	SOT23	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



H62 = Product Type Marking Code
$\overline{Y}$M = Date Code Marking
$\overline{Y}$= Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	F	G	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +100°C	I_D	-2.4 -1.5	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	-13	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-1.6	A
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I_{SM}	-13	A
Avalanche Current , L = 0.1mH			I_{AS}	-12	A
Avalanche Energy , L = 0.1mH			E_{AS}	8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.92	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	165	°C/W
Power Dissipation (Note 6)	P_D	1.62	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6)	$R_{\theta JA}$	93.1	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-1.9	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	112	155	mΩ	V_{GS} = -10V, I_D = -2A
		—	149	240		V_{GS} = -4.5V, I_D = -2A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	512	—	pF	V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	31.3	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	23.2	—	pF	
Gate Resistance	R_g	—	11.9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	4.0	—	nC	V_{DS} = -30V, I_D = -2A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	8.3	—	nC	
Gate-Source Charge	Q_{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.7	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	12.5	—	ns	V_{DD} = -30V, V_{GS} = -10V, I_D = -1.0A, R_G = 50Ω
Turn-On Rise Time	t_R	—	13.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	96.0	—	ns	
Turn-Off Fall Time	t_F	—	39.1	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	9.6	—	ns	I_F = -1A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	3.1	—	nC	I_F = -1A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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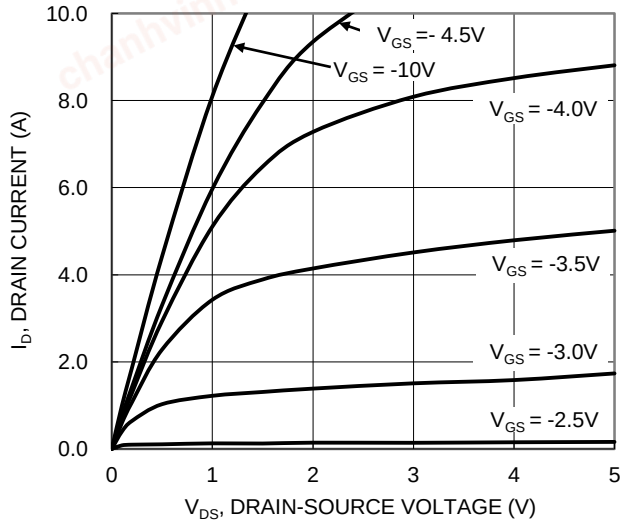


Figure 1. Typical Output Characteristic

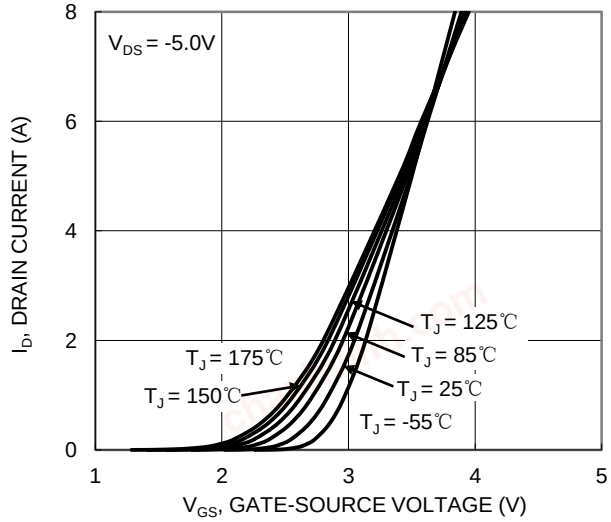


Figure 2. Typical Transfer Characteristic

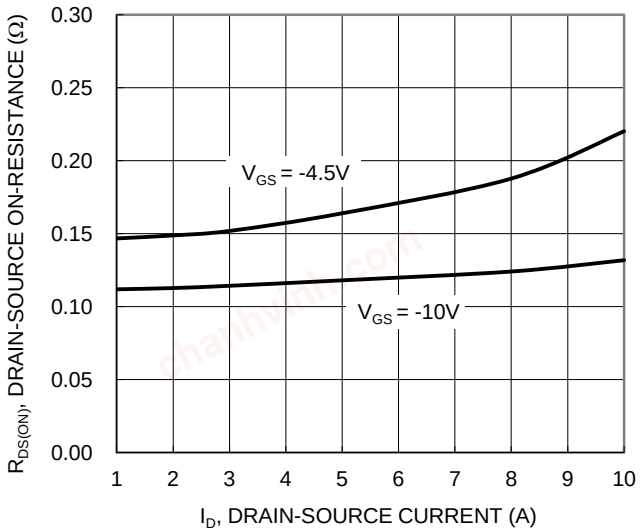


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

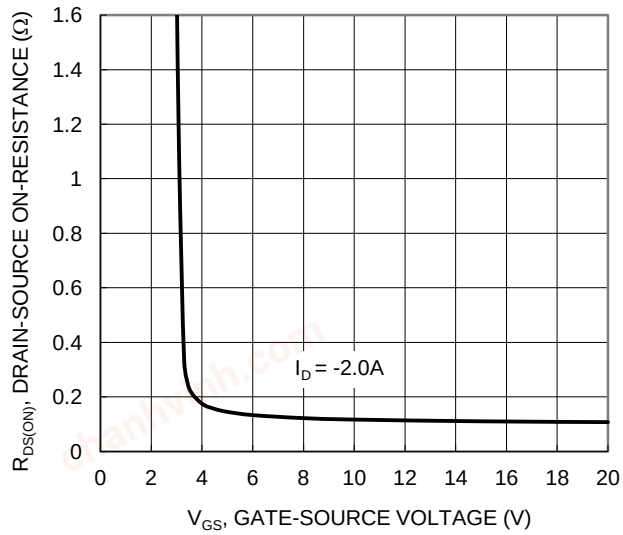


Figure 4. Typical Transfer Characteristic

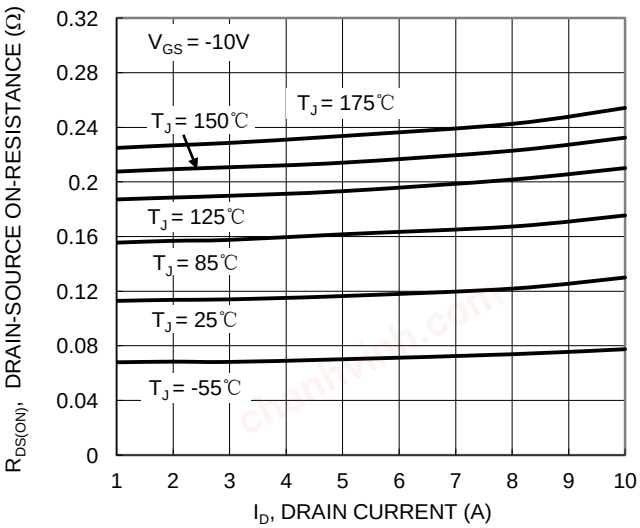


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

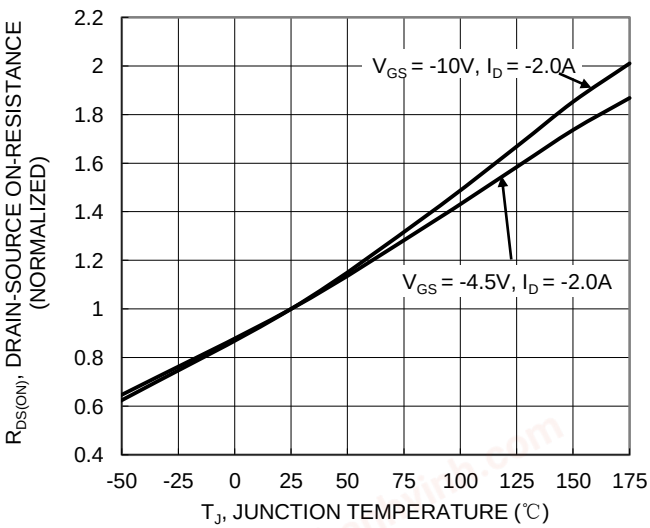


Figure 6. On-Resistance Variation with Temperature

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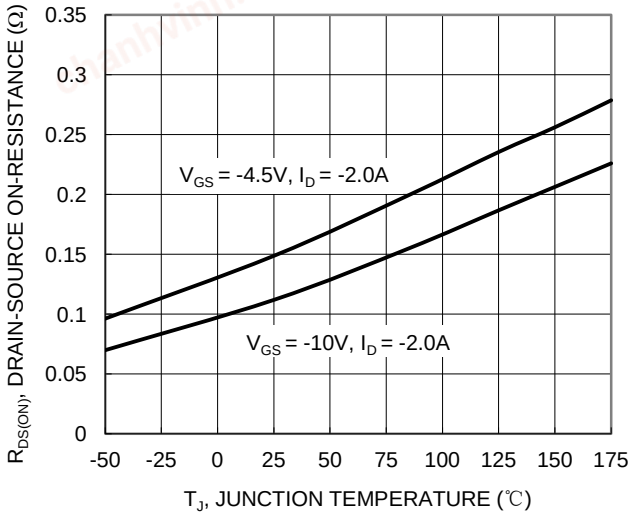


Figure 7. On-Resistance Variation with Temperature

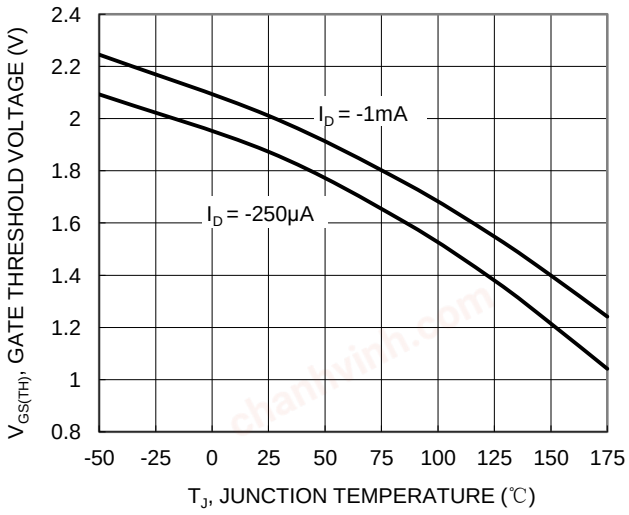


Figure 8. Gate Threshold Variation vs. Junction Temperature

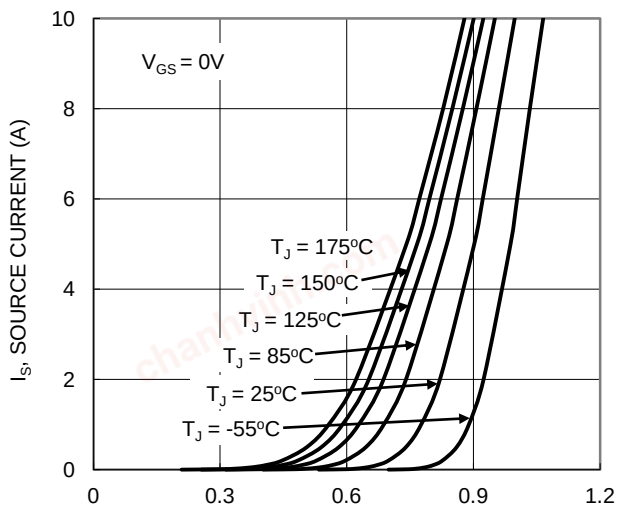


Figure 9. Diode Forward Voltage vs. Current

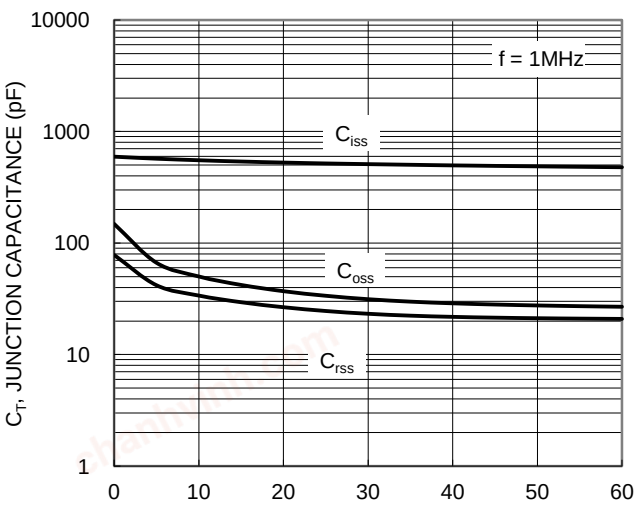


Figure 10. Typical Junction Capacitance

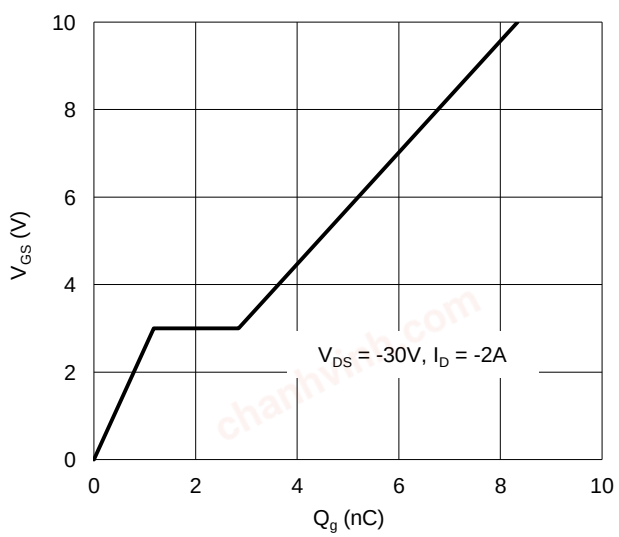


Figure 11. Gate Charge

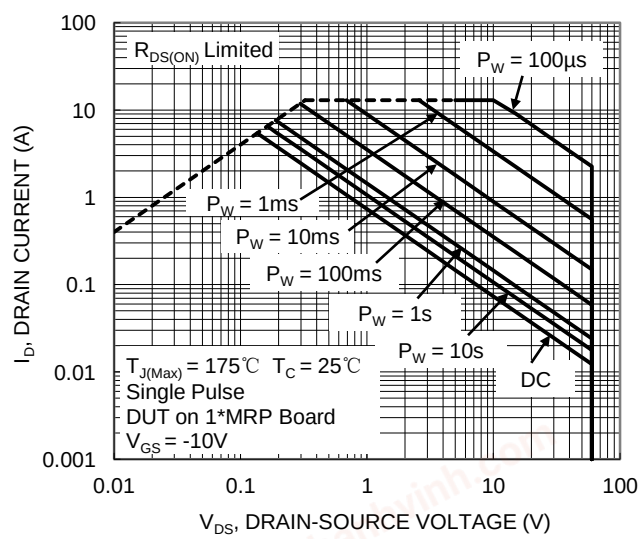


Figure 12. SOA, Safe Operation Area

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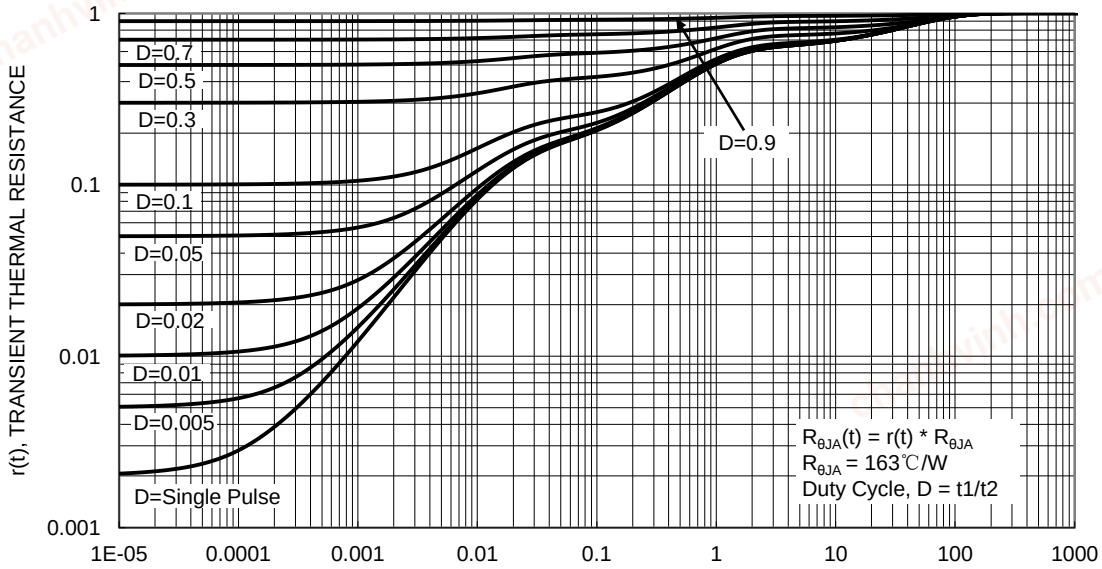


Figure 13. Transient Thermal Resistance

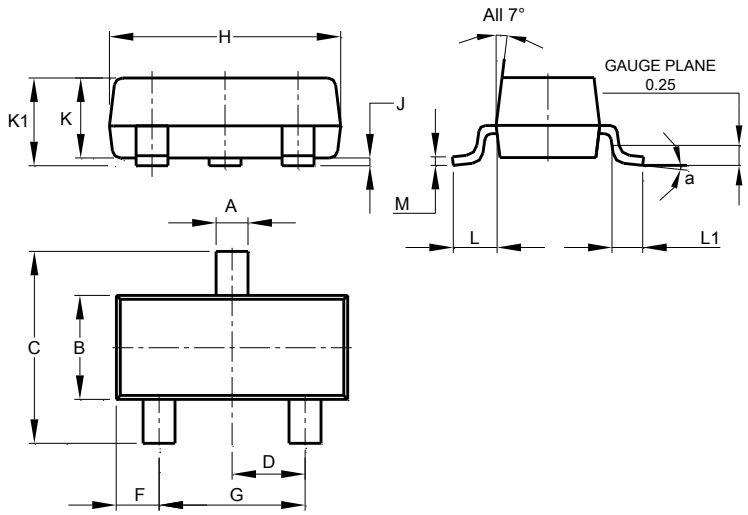
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

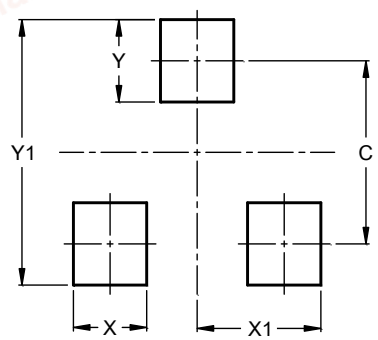


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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